

DESCRIPTION

The IS733 optocoupler consists of two infrared emitting diodes connected in inverse parallel and optically coupled to an NPN silicon transistor in a standard 6 pin dual in line plastic package.

FEATURES

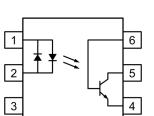
- High AC Isolation voltage 5000V_{RMS}
- Wide Operating Temperature Range
- –40°C to 100°C
- RoHS Compliant
- UL Approval E91231 Model "GG"
- VDE Approval 40028086

APPLICATIONS

- Computer Terminals
- Industrial System Controllers
- AC Input Response
- Signal Transmission between Systems of Different Potentials and Impedances

ORDER INFORMATION

- Add Suffix "X" for VDE Approval
- Add G after PN for 10mm lead spacing
- Add SM after PN for Surface Mount
- Add SMT&R after PN for Surface Mount Tape & Reel





- 1 Anode
- 2 Cathode
- 3 NC
- 4 Emitter
- 5 Collector
- 6 Base

ABSOLUTE MAXIMUM RATINGS $(T_A = 25^{\circ}C)$

Stresses exceeding the absolute maximum ratings can cause permanent damage to the device.

Exposure to absolute maximum ratings for long periods of time can adversely affect reliability.

Input

Forward Current	±50mA
Power Dissipation	70mW

Output

Collector Current	50mA
Collector to Emitter Voltage V_{CEO}	35V
Collector to Base Voltage V_{CBO}	35V
Emitter to Collector Voltage V _{ECO}	6V
Emitter to Base Voltage V _{EBO}	6V
Power Dissipation	150mW

Total Package

Total Power Dissipation	200mW
Isolation Voltage	$5000V_{\text{RMS}}$
Operating Temperature	-40 to 100°C
Storage Temperature	−55 to 125°C
Junction Temperature	125°C
Lead Soldering Temperature (10s)	260°C

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

INPUT

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Forward Voltage	V_{F}	$I_F = \pm 20 \text{mA}$		1.2	1.4	V
Terminal Capacitance	C_{t}	$V_F = 0V$, $f = 1kHz$		50	250	pF

OUTPUT

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector-Emitter Breakdown Voltage	BV _{CEO}	$I_C = 0.1 \text{mA}, I_F = 0 \text{mA}$	35			V
Emitter-Collector Breakdown Voltage	$\mathrm{BV}_{\mathrm{ECO}}$	$I_E=10\mu A,I_F=0mA$	6			V
Collector Dark Current	I_{CEO}	$V_{CE} = 20V, I_F = 0mA$			100	nA

COUPLED

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Current transfer ratio	CTR	$I_F = \pm 1 \text{mA}, V_{CE} = 5 V$	20		300	%
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$I_F = \pm 20 \text{mA}, I_C = 1 \text{mA}$			0.2	V
Floating Capacitance	C_{f}	$V_{IO} = 0V, f = 1MHz$		0.6	1	pF
Cut-Off Frequency	f_{C}	$\begin{aligned} V_{CE} &= 5V, I_C = 2mA \\ R_L &= 100\Omega, -3dB \end{aligned}$	15	80		kHz
Output Rise Time	t _r	$V_{CE} = 2V, I_C = 2mA$ $R_L = 100\Omega$		4	18	μs
Output Fall Time	t_{f}			3	18	μs

ISOLATION

Parameter	Symbol	Test Condition	Min	Тур.	Max	Unit
Isolation Voltage	V _{ISO}	R.H. = 40% to 60%, t = 1 min Note 1	5000			V_{RMS}
Isolation Resistance	R _{I-O}	$V_{\text{I-O}} = 500 \text{VDC}$ R.H. = 40% to 60% Note 1	5x10 ¹⁰	1x10 ¹¹		Ω

Note 1: Measured with input leads shorted together and output leads shorted together.



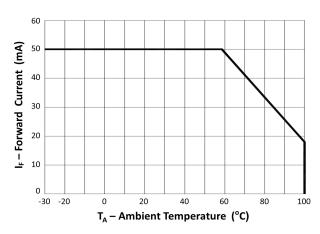


Fig 1 Forward Current vs Ambient Temperature

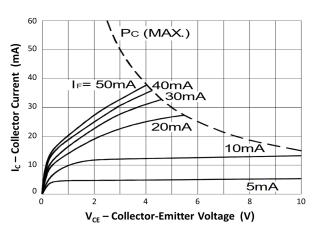


Fig 3 Collector Current vs Collector-Emitter Voltage

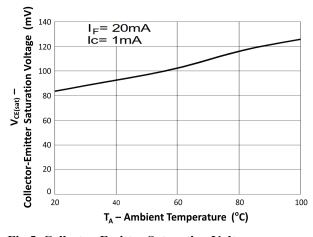


Fig 5 Collector-Emitter Saturation Voltage vs Ambient Temperature

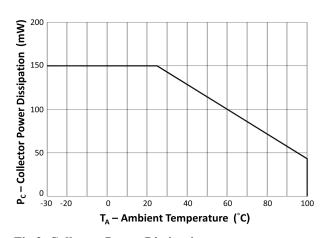


Fig 2 Collector Power Dissipation vs Ambient Temperature

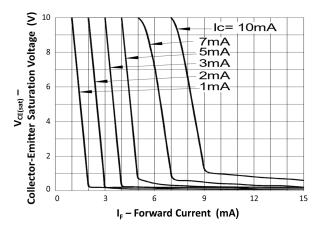


Fig 4 Collector-Emitter Saturation Voltage vs Forward Current

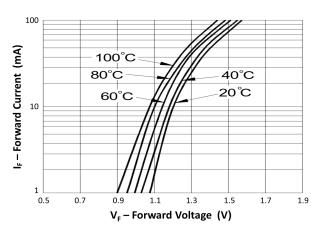


Fig 6 Forward Current vs Forward Voltage



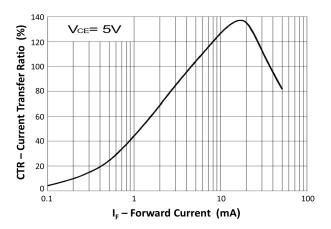


Fig 7 Current Transfer Ratio vs Forward Current

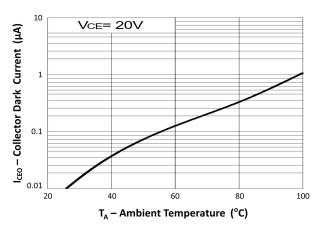


Fig 9 Collector Dark Current vs Ambient Temperature

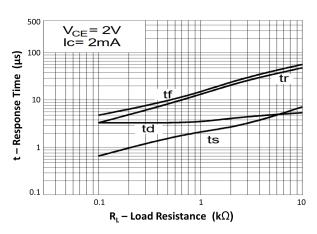


Fig 11 Response Time vs Load Resistance

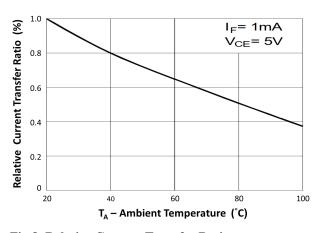


Fig 8 Relative Current Transfer Ratio vs Ambient Temperature

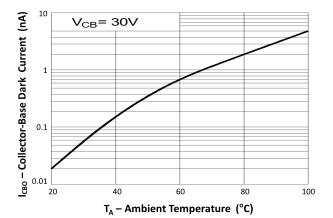


Fig 10 Collector-Base Dark Current vs Ambient Temperature

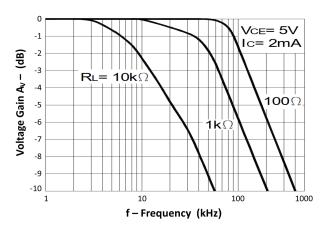


Fig 12 Frequency Response



ORDER INFORMATION

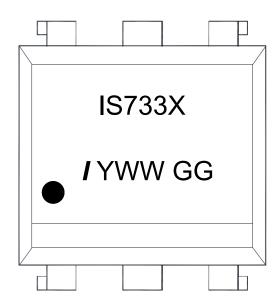
	IS733 (UL Approval)			
After PN	PN	Description	Packing quantity	
None	IS733	Standard DIP6	65 pcs per tube	
G	IS733G	10mm Lead Spacing	65 pcs per tube	
SM	IS733SM	Surface Mount	65 pcs per tube	
SMT&R	IS733SMT&R	Surface Mount Tape and Reel	1000 pcs per reel	

	IS733X (UL and VDE Approvals)				
After PN	PN	Description	Packing quantity		
None	IS733X	Standard DIP6	65 pcs per tube		
G	IS733XG	10mm Lead Spacing	65 pcs per tube		
SM	IS733XGSM	Surface Mount	65 pcs per tube		
SMT&R	IS733XSMT&R	Surface Mount Tape and Reel	1000 pcs per reel		



DEVICE MARKING

Example: IS733X



IS733X denotes Device Part Number

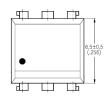
I denotes Isocom

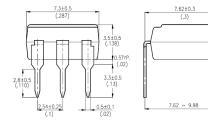
Y denotes 1 digit Year code WW denotes 2 digit Week code



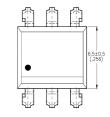
PACKAGE DIMENSIONS (mm)

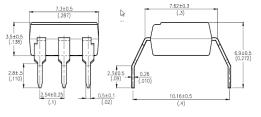
DIP



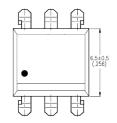


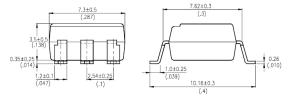
G Form





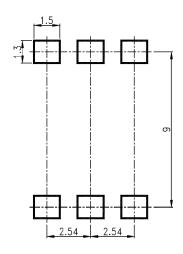
Surface Mount



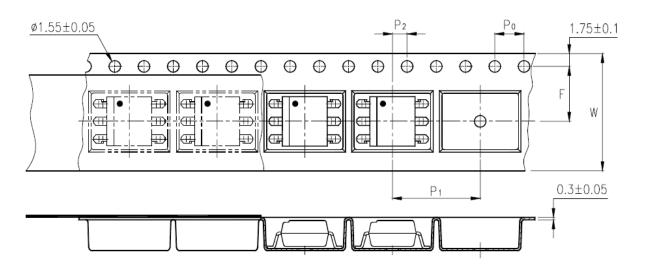




RECOMMENDED PAD LAYOUT FOR SMD (MM)



TAPE AND REEL PACKAGING

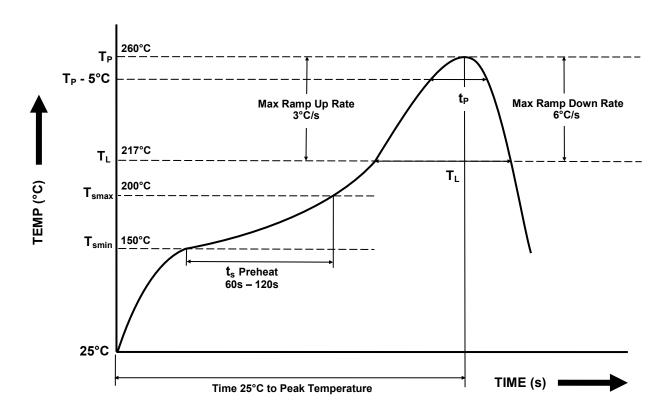


Description	Symbol	Dimension mm (inch)
Tape Width	W	16 ± 0.3 (0.63)
Pitch of Sprocket Holes	P ₀	4 ± 0.1 (0.15)
Distance of Compartment to Sprocket Holes	F	7.5 ± 0.1 (0.295)
Distance of Compartment to Sprocket Holes	P ₂	2 ± 0.1 (0.079)
Distance of Compartment to Compartment	P ₁	12 ± 0.1 (0.472)



IR REFLOW SOLDERING TEMPERATURE PROFILE

One Time Reflow Soldering is Recommended. Do not immerse device body in solder paste.



Profile Details	Conditions
$ \begin{array}{l} \textbf{Preheat} \\ \textbf{- Min Temperature } (T_{SMIN}) \\ \textbf{- Max Temperature } (T_{SMAX}) \\ \textbf{- Time T}_{SMIN} \ \text{to T}_{SMAX} \left(t_s \right) \end{array} $	150°C 200°C 60s - 120s
$ \begin{array}{lll} \textbf{Soldering Zone} \\ & \text{- Peak Temperature } (T_P) \\ & \text{- Time at Peak Temperature} \\ & \text{- Liquidous Temperature } (T_L) \\ & \text{- Time within 5°C of Actual Peak Temperature } (T_P - 5^\circ C) \\ & \text{- Time maintained above } T_L \left(t_L \right) \\ & \text{- Ramp Up Rate } (T_L to T_P) \\ & \text{- Ramp Down Rate } (T_P to T_L) \\ \end{array} $	260°C 10s max 217°C 30s max 60s - 100s 3°C/s max 6°C/s max
Average Ramp Up Rate (T _{smax} to T _P)	3°C/s max
Time 25°C to Peak Temperature	8 minutes max



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